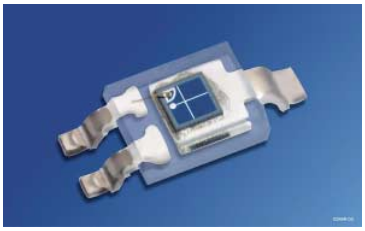
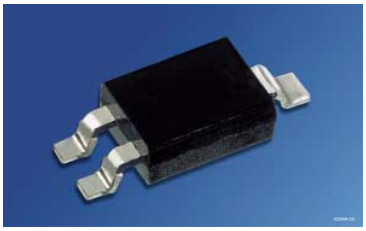
Silizium-PIN-Fotodiode mit sehr kurzer Schaltzeit
Silicon PIN Photodiode with Very Short Switching Time

SFH 2400
SFH 2400 FA



SFH 2400



SFH 2400 FA

Wesentliche Merkmale

- Speziell geeignet für Anwendungen im Bereich von 400 nm bis 1100 nm (SFH 2400) und bei 880 nm (SFH 2400 FA)
- Kurze Schaltzeit (typ. 5 ns)
- SMT-Bauform, geeignet für Vapor Phase-Löten und IR-Reflow-Löten (JEDEC level 4)
- Nur gegurtet lieferbar

Features

- Especially suitable for applications from 400 nm to 1100 nm (SFH 2400) and of 880 nm (SFH 2400 FA)
- Short switching time (typ. 5 ns)
- SMT package, suitable for vapor phase and IR reflow soldering (JEDEC level 4)
- Available only on tape and reel

Anwendungen

- Industrieelektronik
- „Messen/Steuern/Regeln“
- Schnelle Lichtschranken für Gleich- und Wechsellichtbetrieb

Applications

- Industrial electronics
- For control and drive circuits
- Photointerrupters

Typ Type	Bestellnummer Ordering Code	Gehäuse Package
SFH 2400	Q62702-P1794	Klares Epoxy-Gießharz, Kathodenkennzeichung: breiter Anschluß Transparent epoxy resin, cathode marking: broad lead
SFH 2400 FA	Q62702-P5035	Schwarzes Epoxy-Gießharz, Kathodenkennzeichung: breiter Anschluß Black epoxy resin, cathode marking: broad lead

Grenzwerte
Maximum Ratings

Bezeichnung **Parameter**	**Symbol** **Symbol**	**Wert** **Value**	**Einheit** **Unit**
Betriebs- und Lagertemperatur Operating and storage temperature range	T_{op}; T_{stg}	– 40 … + 100	°C
Sperrspannung Reverse voltage	V_R	20	V
Sperrspannung t < 2 min Reverse voltage t < 2 min	V_R	50	V
Verlustleistung Total power dissipation	P_{tot}	120	mW
Wärmewiderstand für Montage auf PC-Board Thermal resistance for mounting on pcb	R_{thJA}	450	K/W

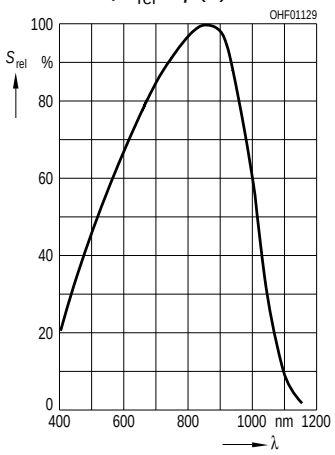
Kennwerte (T_A = 25 °C)
Characteristics

Bezeichnung **Parameter**	**Symbol** **Symbol**	**Wert** **Value**		**Einheit** **Unit**
		SFH 2400	**SFH 2400 FA**	
Fotostrom Photocurrent V_R = 5 V, Normlicht/standard light A, T = 2856 K, E_V = 1000 lx	I_P	10 (> 6)	–	µA
V_R = 5 V, λ = 870 nm, E_e = 1 mW/cm²	I_P	6.5	6.2 (≥ 3.6)	µA
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S\ max}$	850	900	nm
Spektraler Bereich der Fotoempfindlichkeit S = 10% von S_{max} Spectral range of sensitivity S = 10% of S_{max}	λ	400 … 1100	750 … 1100	nm
Bestrahlungsempfindliche Fläche Dimensions of radiant sensitive area	$L \times B$ $L \times W$	1 × 1	1 × 1	mm × mm
Chipgröße Chip size	$L \times B$ $L \times W$	1.4 × 1.4	1.4 × 1.4	mm × mm
Halbwinkel Half angle	φ	± 60	± 60	Grad deg.

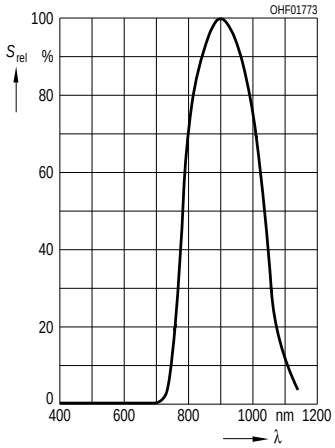
Kennwerte (T_A = 25 °C)
Characteristics (cont'd)

Bezeichnung **Parameter**	**Symbol** **Symbol**	**Wert** **Value**		**Einheit** **Unit**
		SFH 2400	**SFH 2400 FA**	
Dunkelstrom, V_R = 20 V Dark current	I_R	1 (< 5)	1 (< 5)	nA
Leerlaufspannung Open-circuit voltage E_v = 1000 lx, Normlicht/standard light A, T = 2856 K E_e = 1 mW/cm², λ = 870 nm	 V_O V_O	 320 –	 – 320	 mV mV
Kurzschlußstrom Short-circuit current E_v = 1000 lx, Normlicht/standard light A, T = 2856 K E_e = 1 mW/cm², λ = 870 nm	 I_{SC} I_{SC}	 10 –	 – 6.0	 µA µA
Anstiegs- und Abfallzeit des Fotostromes Rise and fall time of the photocurrent R_L = 50 Ω; V_R = 20 V; λ = 850 nm; I_p = 800 µA	t_r, t_f	5	5	ns
Durchlaßspannung, I_F = 80 mA, E = 0 Forward voltage	V_F	1.3	1.3	V
Kapazität, V_R = 0 V, f = 1 MHz, E = 0 Capacitance	C_0	11	11	pF
Temperaturkoeffizient von V_O Temperature coefficient of V_O	TC_V	– 2.6	– 2.6	mV/K
Temperaturkoeffizient von I_{SC} Temperature coefficient of I_{SC} Normlicht/standard light A λ = 870 nm	TC_I	 0.18 –	 – 0.2	%/K
Rauschäquivalente Strahlungsleistung Noise equivalent power V_R = 20 V, λ = 870 nm	NEP	2.9×10^{-14}	2.9×10^{-14}	$\frac{W}{\sqrt{Hz}}$
Nachweisgrenze, V_R = 20 V, λ = 870 nm Detection limit	D*	3.5×10^{12}	3.5×10^{12}	$\frac{cm \times \sqrt{Hz}}{W}$

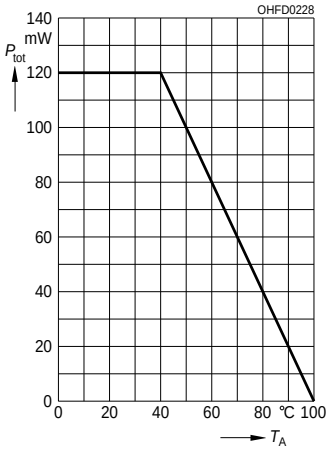
Relative Spectral Sensitivity
SFH 2400, $S_{rel} = f(\lambda)$



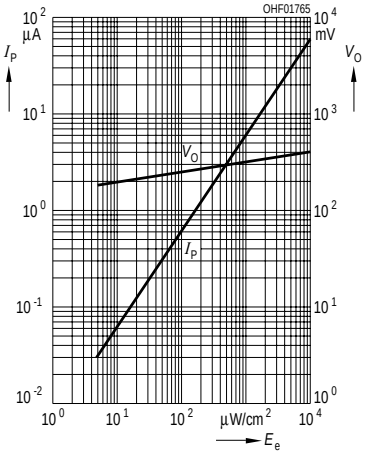
Relative Spectr. Sensitivity
SFH 2400 FA, $S_{rel} = f(\lambda)$



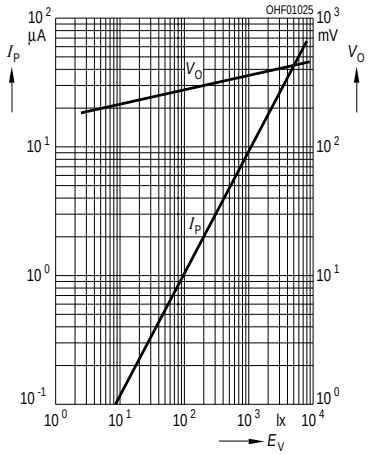
Total Power Dissipation
$P_{tot} = f(T_A)$



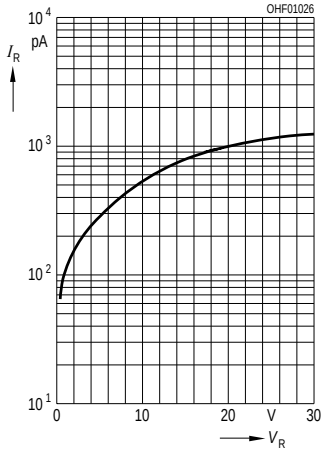
Photocurrent $I_P = f(E_e)$, $V_R = 5$ V
Open-Circuit Voltage $V_O = f(E_e)$
SFH 2400 FA



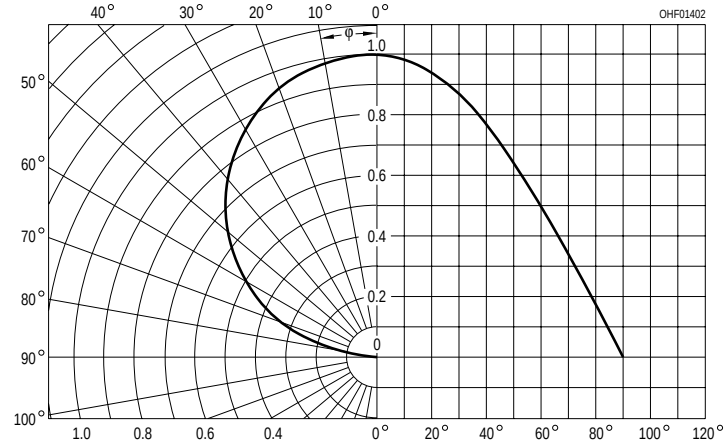
Photocurrent $I_P = f(E_v)$, $V_R = 5$ V
Open-Circuit Voltage $V_O = f(E_v)$
SFH 2400



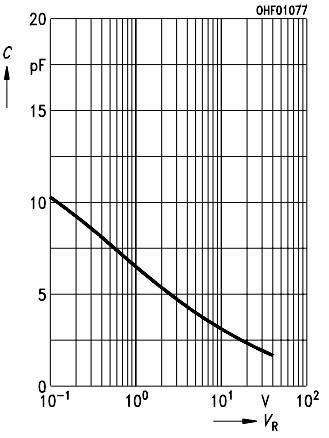
Dark Current
$I_R = f(V_R)$, $E = 0$



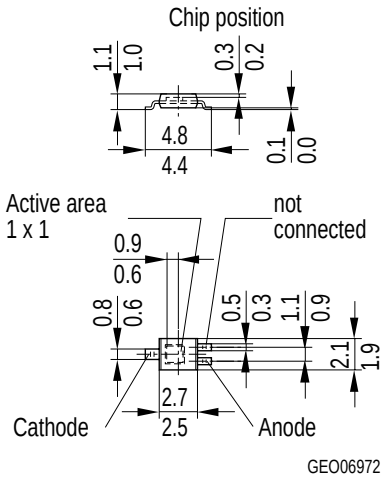
Directional Characteristics
$S_{rel} = f(\varphi)$



Capacitance
$C = f(V_R)$, $f = 1$ MHz, $E = 0$



Maßzeichnung
Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

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